

Title (en)  
Substrate processing unit

Title (de)  
Substratbearbeitungseinheit

Title (fr)  
Unité de traitement de substrats

Publication  
**EP 1215715 A3 20060628 (EN)**

Application  
**EP 01120274 A 20010823**

Priority  
JP 2000377785 A 20001212

Abstract (en)  
[origin: EP1215715A2] A substrate processing unit 10 capable of restraining contaminants such as particles, watermarks and the like from being adhered to a substrate such as a semiconductor wafer and the like, wherein the substrate processing unit 10 comprises a processing bath 11 for accommodating the substrates (e.g., wafer W) to be processed, a processing fluid introduction pipe 21 for supplying processing fluid (e.g., purified water J) to the processing bath 11, a vapor generating bath 61 for accommodating an organic solvent S (e.g., IPA fluid), a processing fluid discharge section 30 for discharging processing fluid from the processing bath 11, and a solvent heating unit 62 for heating the organic solvent S inside the vapor generating bath 61, wherein the vapor generating bath 61 introduces vapor generated from the organic solvent S to the inside of the processing bath 11, and the solvent heating unit 62 heats the organic solvent S inside the vapor generating bath 61 at a temperature in the range of 50°C±5°C if a surface of the wafer W is hydrophobic and heats the organic solvent S at a temperature in the range of 70°C±5°C if the surface of the wafer W is hydrophilic.

IPC 8 full level  
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Citation (search report)

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- [A] US 5078832 A 19920107 - TANAKA MASATO [JP]
- [A] US 4984597 A 19910115 - MCCONNELL CHRISTOPHER F [US], et al
- [XA] PATENT ABSTRACTS OF JAPAN vol. 1999, no. 08 30 June 1999 (1999-06-30)

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